

Title (en)
SILICON BIPOLAR TRANSISTOR, CIRCUIT ARRANGEMENT AND METHOD FOR PRODUCTION OF A SILICON BIPOLAR TRANSISTOR

Title (de)
SILIZIUM-BIPOLARTRANSISTOR, SCHALTUNGSANORDNUNG UND VERFAHREN ZUM HERSTELLEN EINES SILIZIUM-BIPOLARTRANSISTORS

Title (fr)
TRANSISTOR BIPOLAIRE AU SILICIUM, ENSEMBLE CIRCUIT ET PROCEDE DE FABRICATION D'UN TRANSISTOR BIPOLAIRE AU SILICIUM

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Application
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Abstract (en)
[origin: WO0197273A1] The silicon bipolar transistor (100) comprises a base, with a first highly-doped base layer (105) and a second poorly-doped base layer (106) which together form the base. The emitter is completely highly-doped and mounted directly on the second base layer (106).

IPC 1-7
H01L 21/331; **H01L 29/737**; **H01L 29/732**

IPC 8 full level
H01L 21/331 (2006.01); **H01L 21/22** (2006.01); **H01L 29/10** (2006.01); **H01L 29/732** (2006.01); **H01L 29/737** (2006.01)

CPC (source: EP KR US)
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Citation (search report)
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